



Peak pulse voltage ( $T_j=25$ ; non-repetitive, off-state; FIG.8)	$V_{pp}$	4	kV
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**ELECTRICAL CHARACTERISTICS** ( $T_j=25$  unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
$I_{GT}$	$V_D=12V$ $R_L=33$	- -	MAX.	35	mA
$V_{GT}$		- -	MAX.	1	V
$V_{GD}$	$V_D=V_{DRM}$ $T_j=150$ $R_L=3.3k$	- -	MIN.	0.2	V
$I_L$	$I_G=1.2I_{GT}$	-	MAX.	50	mA
				60	
$I_H$	$I_T=100mA$		MAX.	35	mA
$dV/dt$	$V_D=540V$ Gate Open $T_j=150$		MIN.	1200	V/ $\mu s$
$(dI/dt)_c$	$(dV/dt)_c=20V/\mu s$ , $T_j=150$		MIN.	8	A/ms
$t_{on}$	$I_G=40mA$ $I_A=200mA$ $I_R=20mA$ $T_j=25$		TYP.	3	$\mu s$
$t_{off}$				30	

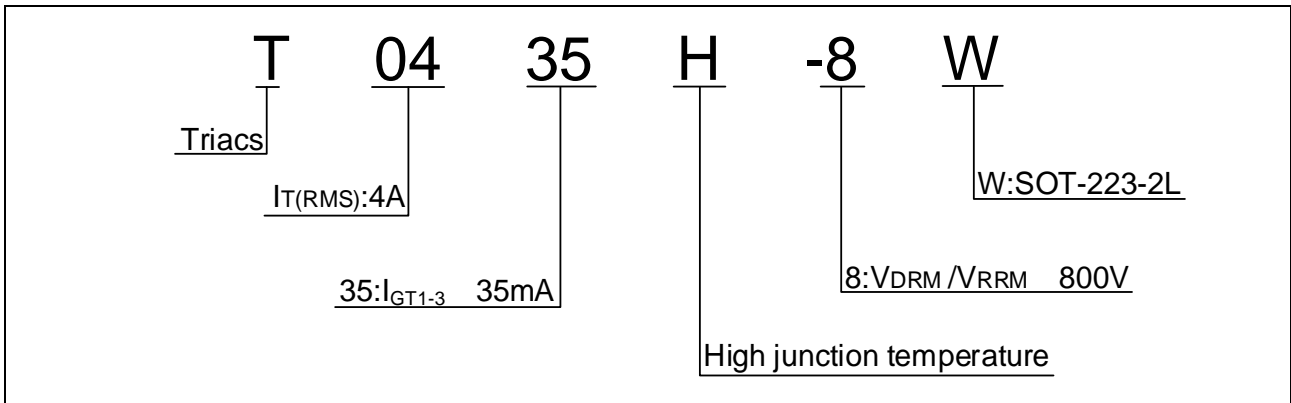
**STATIC CHARACTERISTICS**

Symbol	Parameter		Value(MAX.)	Unit
$V_{TM}$	$I_{TM}=5A$ $t_p=380\mu s$	$T_j=25$	1.5	V
$V_{TO}$	Threshold voltage	$T_j=150$	0.63	V
$R_D$	Dynamic resistance	$T_j=150$	324	m
$I_{DRM}$	$V_D=V_{DRM}$ $V_R=V_{RRM}$	$T_j=25$	5	$\mu A$
$I_{RRM}$		$T_j=150$	1	mA

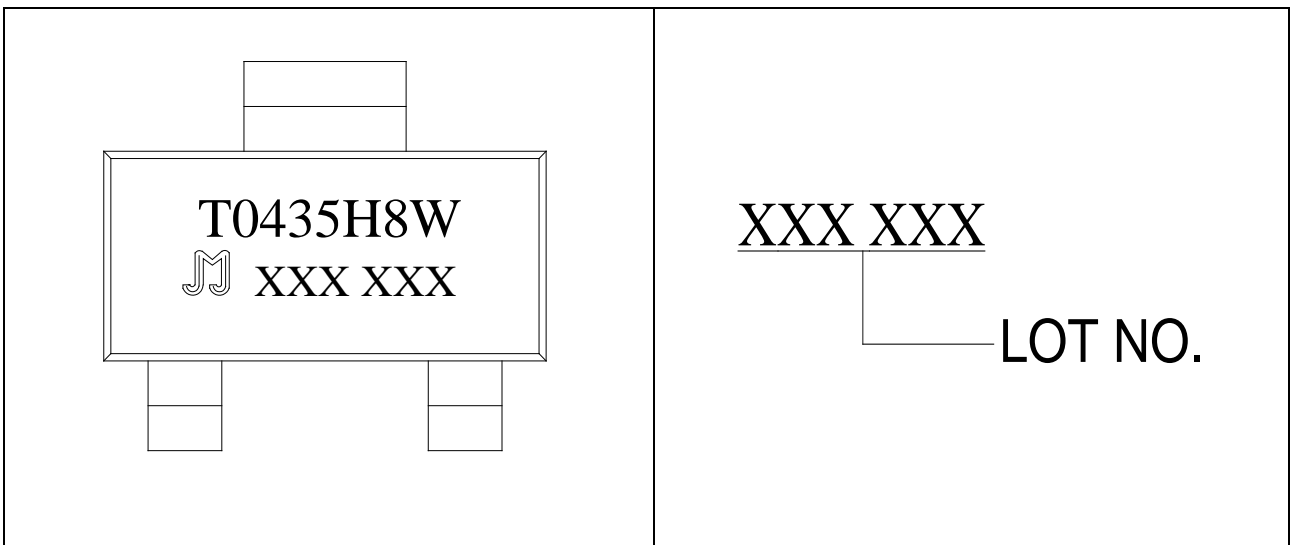
**THERMAL RESISTANCES**

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	17	$^{\circ}W$
$R_{th(j-a)}$	junction to ambient (AC)	60	$^{\circ}W$

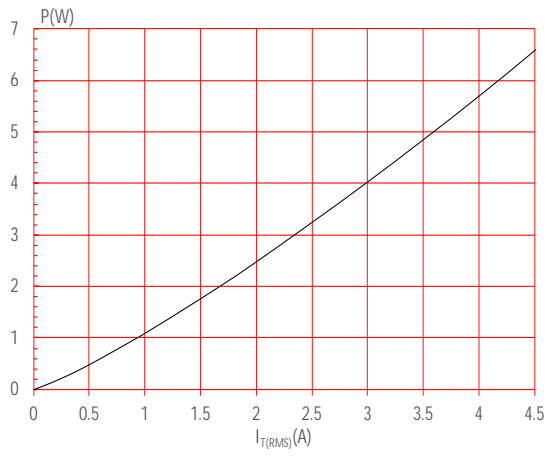
ORDERING INFORMATION



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**FIG.1:** Maximum power dissipation versus RMS on-state current



**FIG.2:** RMS on-state current versus case temperature

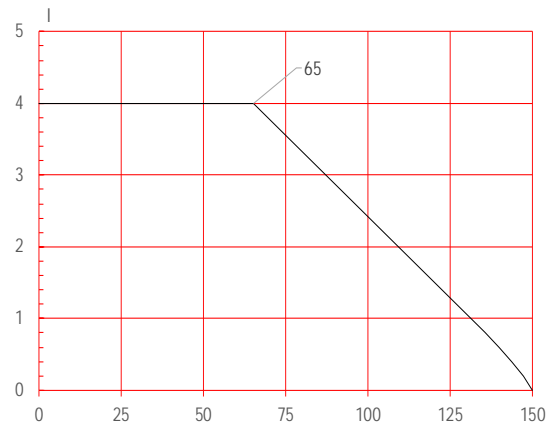


FIG.7: Relative variations of gate trigger current, holding current and latching current versus junction temperature

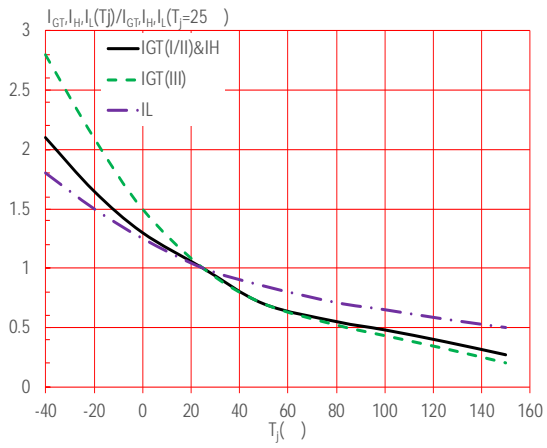
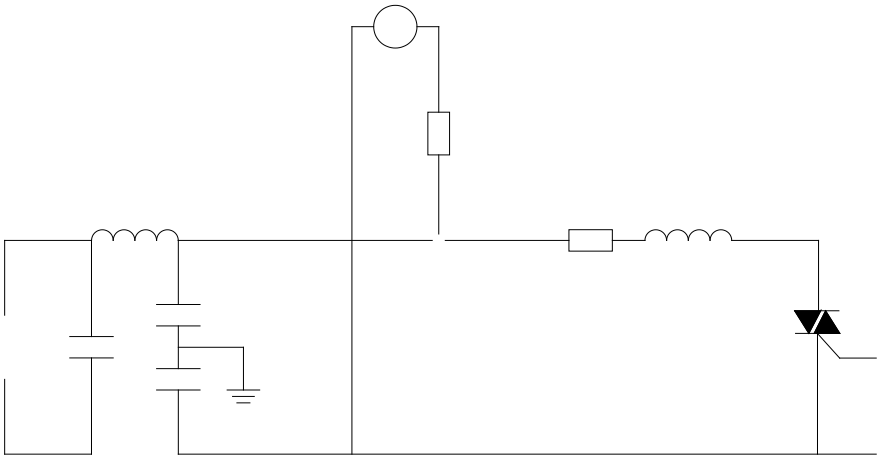


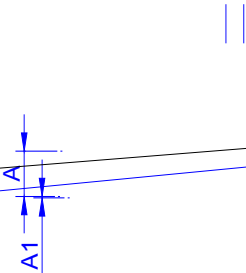
FIG.8 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



**T0435H-8W**

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PACKAGE MECHANICAL DATA





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